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Sheet		1	of		1
		Application Number		10/743,906	
		Filing Date		12/24/2003	
		First Named Inventor		Ryu OGIWARA et al.	
		Group Art Unit		2824	
		Examiner Name		Unknown	
		Attorney Docket Number		001701.00198	

U.S. PATENT DOCUMENTS						
Examiner Initials *	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
at		5,903,492	B1	Takashima	05/1999	365/145
at		6,094,370	B1	Takashima	07/2000	365/145
at		6,300,654	B1	Corvasce et al.	10/2001	257/296
at		6,483,737	B2	Takeuchi et al.	11/2002	365/145

FOREIGN PATENT DOCUMENTS								
Examiner Initials *	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ₆
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
at		EP	0 631 287	A	Ramtron Int.	12/1994	611C 11/22	X
at		DE	197 24 449	A	Toshiba	12/1997	611C 11/22	Abst
at		JP	10-255483		Toshiba	09/1998	611C 14/00	Abst
at		JP	11-177036		Toshiba	07/1999	HOLL 27/10	Abst

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
at		D. Takashima, et al., "Gain Cell Block Architecture for Gigabit-Scale Chain Ferroelectric RAM," 1999 Symposium on VLSI Circuits, pp. 103-104	
at		D. Takashima et al., "High-Density Chain Ferroelectric Random-Access Memory (CFRAM)," Symposium on VLSI Circuits Digest of Technical Papers, 1997, pp. 83-84	
at		D. Takashima et al., "A Sub-40ns Random-Access Chain FRAM Architecture with a 7ns Cell-Plate-Line Drive," ISSCC Digest of Technical Papers, February 15, 1999, pp. 102-103, and 450	

Examiner Signature		Date Considered	01/13/2006
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